

**Notice of References Cited**

Application/Control No.  
09/912,558

Applicant(s)/Patent Under  
Reexamination  
WEIMER ET AL.

Examiner  
Erik Kielin

Art Unit  
2813

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
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	B	US-6,197,668	03-2001	Gardner et al.	438/180
	C	US-2001/0020725	09-2001	Okuno et al.	257/410
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	K	US-			
	L	US-			
	M	US-			

**FOREIGN PATENT DOCUMENTS**

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	N					
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**NON-PATENT DOCUMENTS**

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Luan, et al. "Ultra thin high quality Ta <sub>2</sub> O <sub>5</sub> gate dielectric prepared by in-situ rapid thermal processing" Electron Devices Meeting, held 6-9 December 1998, IEDM '98 Technical Digest, pp. 609-612.
	V	Lu et al. "Leakage current comparison between ultra-thin Ta <sub>2</sub> O <sub>5</sub> films and conventional gate dielectrics" IEEE Electron Device Letters 19(9), 9/1998, pp. 341-342.
	W	Alders, et al. "Intermixing at the tantalum oxide/silicon interface in gate dielectric structures" Applied Physics Letters 73(11), 14 September 1998, pp. 1517-1519.
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\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.